NPN SILICON RF POWER TRANSISTOR

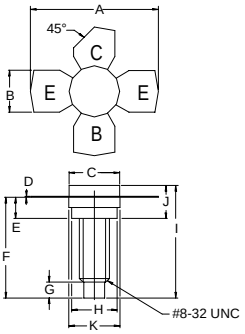
DESCRIPTION:

The **ASI BFQ34** is primarily designed for driver and final stages in MATV system amplifier up to 4.0 GHz.

FEATURES:

- P_G = 12 dB min. at 3 W/ 400 MHz
- η_C = 50% min. at 3W/ 400 MHz
- ***Omnigold***™ Metallization System
- Diffused Emitter-Ballasting resistors

PACKAGE STYLE .280 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 /5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

MAXIMUM RATINGS

I_C	150 mA
V_{CBO}	25 V
V_{CEO}	18 V
P_{DISS}	2.7 W @ T_C = 160 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	15 K/W

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 20 mA	18			V
BV_{CBO}	I_C = 5.0 mA	25			V
BV_{EBO}	I_E = 5.0 mA	2.0			V
I_{CBO}	V_{CB} = 15 V			100	µA
h_{FE}	V_{CE} = 15 V I_C = 75 mA V_{CE} = 15 V I_C = 150 mA	25 25	70 70		---
C_c	V_{CB} = 15 V f = 1.0 MHz		2.0	2.75	pF
G_{UM} F	V_{CE} = 15 V I_C = 120 mA f = 500 MHz		16.3 8.0		dB dB